

Diffusion and submonolayer island growth during hyperthermal deposition on Cu(100) and Cu(111)

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Abstract

We consider the influence of realistic island diffusion rates to homoepitaxial growth on metallic surfaces using a recently developed rate equation model which describes growth in the submonolayer regime with hyperthermal deposition. To this end, we incorporate realistic size and temperature-dependent island diffusion coefficients for the case of homoepitaxial growth on Cu(100) and Cu(111) surfaces. We demonstrate that the generic features of growth remain unaffected by the details of island diffusion, thus validating the generic scenario of high density of small islands found experimentally and theoretically for large detachment rates. However, the details of the morphological transition and scaling of the mean island size are

strongly influenced by the size dependence of island diffusion. This is reflected in the scaling exponent of the mean island size, which depends on both temperature and the surface geometry.

Key words: submonolayer island growth, hyperthermal deposition, diffusion, copper

1 Introduction

Hyperthermal deposition (HTD) techniques, such as ion-beam assisted deposition (IBAD) and low-energy ion deposition (LEID) [1] have recently been shown to have great potential in controlling and improving the properties of thin films as grown by molecular beam epitaxy. In HTD the island density is larger, the average island size is smaller [2,3], and island size distributions are considerably broader [1,3] than in ordinary thermal deposition. Possible atomistic processes responsible for these effects include ion enhanced mobilities, cluster dissociation [1], and defect creation during deposition [2,4].

A particularly striking observation made in the LEID experiments is that with different deposition energies an anomalously high density of small islands is observed, with the scaled distribution function behaving as $f(x) \sim 1/x$ for $x < 1$ [1]. We have recently shown using the rate equation (RE) approach [5,6] that this anomalously high density of small islands is due to a unique balance between island–island aggregation and enhanced adatom detachment. These studies were aimed at describing the generic features of HTD, and thus

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relatively idealized approximations for the terms in the rate equations were used to obtain analytical estimates for the relevant growth exponents and the scaling function. One of the most important questions that still remains open is the role of *island diffusion*, since for mobile islands the aggregation rates in the RE approach depend explicitly on the diffusion coefficients D_s of islands of different sizes s . Island diffusion on surfaces has been studied both theoretically [7,8,9] and experimentally [10,11,12,13,14,15,16]. While in the large island limit the size dependence of the island diffusion coefficients can be classified based on simple basic processes [17], for smaller islands D_s depends on the geometric and energetic details of the underlying surface, and can be a complicated, non-monotonic function of s [18,19].

In this work, our aim is to explore in detail the influence of realistic island diffusion coefficients to submonolayer growth with HTD. To this end, we employ the RE model of Ref. [5] and replace the usually assumed idealized power law forms of D_s with realistic, temperature and size-dependent diffusion coefficients $D_s(T)$ for Cu on Cu(100) and Cu(111) surfaces. These two systems highlight the large differences which occur for surfaces with different geometry and energetics. We demonstrate that while the scaling function of the size distribution is largely unaffected by the details of the diffusion coefficients, the quantitative values of the growth exponents are sensitive to island diffusion. These predictions can be easily tested by HTD experiments on different Cu surfaces.

2 Model

In HTD the reversibility of growth is manifested through enhanced adatom detachment from islands [1,4]. Detachment and island mobility allow us to neglect spatial correlations between islands [20,21,22,23], which justifies the rate equation description of the problem. Thus, growth is driven by the interplay between aggregation and detachment, and can be schematically expressed to be composed of reversible events $A_i + A_j \rightarrow A_{i+j}$; $A_j \rightarrow A_1 + A_{j-1}$ between islands of sizes i and j with the rates of aggregation and detachment specified by reaction rates $K(i, j)$ and $F(i, j)$, respectively. The corresponding REs for the areal density n_s of islands of size $s \geq 1$ read as [23,24]

$$\frac{dn_s}{dt} = \frac{1}{2} \sum_{i+j=s} [K(i, j)n_i n_j - F(i, j)n_s] - \sum_{j=1}^{\infty} [K(s, j)n_s n_j - F(s, j)n_{s+j}] + \Phi \delta_{1s}, \quad (1)$$

where Φ is the deposition flux of adatoms in monolayers per second (ML/s).

The aggregation rate $K(i, j)$ for islands of sizes i and j with diffusivities D_i and D_j is given by the Smoluchowski formula $K(i, j) \propto (D_i + D_j)$, which is also consistent with the point island approximation used here [20,24]. Previously [5] we used a power-law form for the diffusion coefficients $D_i \sim i^{-\mu}$ with $1 \leq \mu \leq 2$ appropriate for island diffusion on metal surfaces. In order to study the effects of details of the aggregation rates in observable quantities we replace the idealized power-law form by realistic size and temperature dependent diffusion coefficients, as discussed below in more detail.

The detachment rate of adatoms from islands of size $i + j = s$ depends on the island size, but only detachment of single adatoms is allowed. Thus the

detachment rate is given by $F(i, j) = F_0(i + j)^\alpha(\delta_{1i} + \delta_{1j})$, where the exponent α is in principle a parameter, but is chosen to be $\alpha = 1/2$ in the present study. In LEID this form for the detachment rate is physically a well justified choice, because in the regime of bombarding energies from 10 eV to 100 eV adatom detachment dominates and island breakup into larger pieces is not expected to occur [4,25]. Moreover, since every deposition event at the vicinity of an island boundary can be assumed to detach adatoms at least with a probability proportional to the island perimeter (i.e. $s^{1/2}$), $\alpha = 1/2$ is a reasonable lower limit. This has been also confirmed by recent Molecular Dynamics simulations on ion bombardment enhanced detachment in island size region up to 25 atoms where values of $0.4 < \alpha < 0.6$ were found [25].

We solve the rate equations using the particle coalescence method (PCM) [22,20,24]. PCM employs a point-island approximation, which is valid at low coverages or large island separations. In PCM aggregation and detachment events occur with probabilities specified by the corresponding reaction kernels, and the deposition with the rate proportional to the given adatom flux. An event is then randomly chosen with a probability weighted by the corresponding rate. Since REs describe the system in the mean-field limit, there is no information on spatial correlations in the system. Therefore, in the simulations it is sufficient to construct a list of islands, which does not correspond to a physical lattice. To conduct an aggregation event, for example, two islands are randomly chosen from the list, and an attempt to aggregate them is made. The complete mixing of the islands required by the mean-field approximation [22] is thus implemented much faster than including island jumps into empty lattice sites [24].

3 Diffusion Coefficients

In reality the diffusion coefficients of islands depend on island size non-trivially, and not simply as power laws. They can even oscillate as a function of the island size [10,14,8]. These oscillations can be in part understood by the surface geometry: certain close packed island configurations can be more stable than others on certain surfaces [19]. Here we concentrate on two qualitatively and quantitatively different types of diffusion coefficients, namely those of Cu adatom islands on Cu(100) and Cu(111) surfaces.

First, the diffusion coefficients $D_s(T)$ from kinetic Monte Carlo (KMC) simulations, which were based on effective medium theory energetics for the Cu(100) surface, are shown in Fig. 1 at three different temperatures $T = 300, 500,$ and 700 K [8]. At the lowest temperatures the oscillations as a function of s are clearly seen. As temperature increases, the oscillations dampen, and at the highest temperature the diffusion coefficient is rather well described by $D(s) \sim s^{3/2}$, if island diffusion is limited by atomic motion along the perimeter of an island [17]. For Cu(100), there is a strong dependence of D_s on temperature here because the single adatom diffusion barrier is about 0.4 eV.

In contrast to the behavior on Cu(100), island diffusion on Cu(111) follows a completely different trend. The most spectacular difference is the almost complete absence of oscillations in the diffusion coefficient with size for the smaller islands (1 – 10 atoms) [26]. This is seen to occur when small islands diffuse via occupancy of both hcp and fcc sites. Also, there is relatively little temperature dependence on $D_s(T)$ for small sizes, since the surface is relatively smooth with an adatom activation energy of 0.026 eV, and almost the

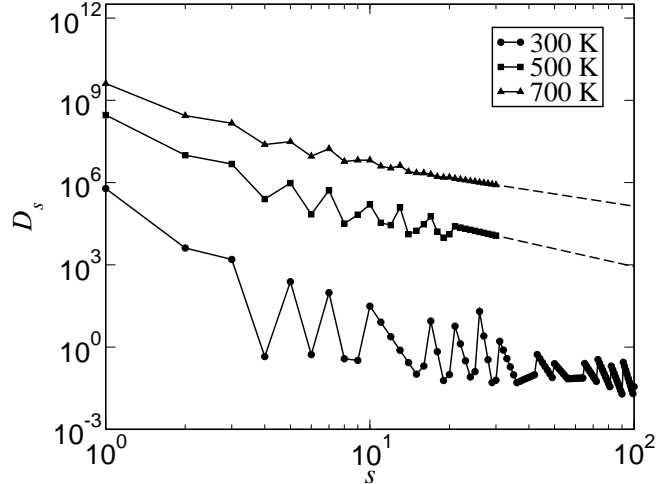


Fig. 1. Size and temperature dependence of diffusion coefficients for 2D adatom islands on Cu(100) at three different temperatures from the KMC simulations of Ref. [8]. For the largest island sizes the data approximately follow the power law $D_s \sim s^{3/2}$.

same for dimers and trimers. In the case of Cu(111), the calculations were carried out using a KMC procedure in which the system is allowed to evolve according to diffusion processes of its choice. This is facilitated through the automatic generation of a database of possible diffusion processes and their activation energy barriers calculated using embedded atom method potentials. The storage and retrieval of information from the database is done via a pattern recognition scheme [27]. From simulations performed at $T = 300$ K, 500 K, and 700 K, the effective diffusion barriers are found to increase almost monotonically with size, while the diffusion coefficient takes the form shown in Fig. 2. Calculations performed for larger sized islands (19 – 100) show a power law scaling of D with island size and with an exponent of about 1.57 which is mildly temperature dependent [28]. This is consistent with the theoretical value of $3/2$ for large island motion dominated by atom diffusion along island perimeter [17].

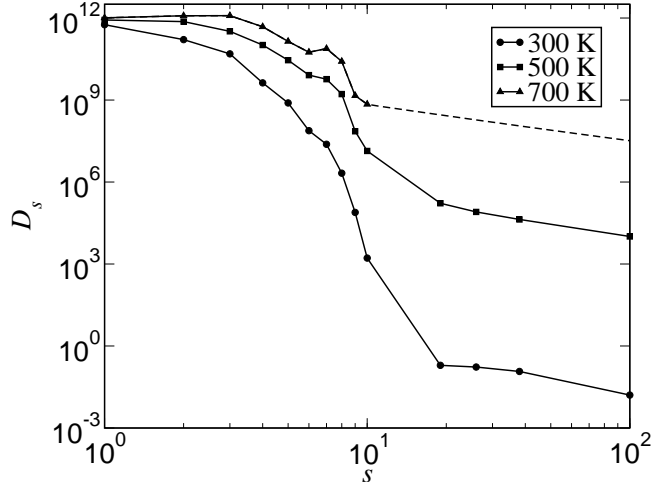


Fig. 2. Size and temperature dependence of diffusion coefficients for 2D adatom islands on Cu(111) at three different temperatures from the KMC simulations. The dashed lines indicate fit to a $s^{-3/2}$ power law [17].

4 Scaling

In our previous study [5] the island size distributions were of the scaling form and the mean island size had a power-law form. Therefore, even if the detachment rate was not a homogeneous function of the island size, we could extract well-defined effective scaling exponents for the mean island size and the size distribution function. In the present case, we expect that scaling is invalidated due to realistic diffusion coefficients which have a naturally inhomogeneous form. There is no guarantee of either the existence of usual scaling type of solutions or uniquely defined scaling exponents for the mean island size and island density. Thus, e.g. the dynamic exponent for the mean island size can be expected to be model-dependent, i.e. we could obtain different values for different sets of diffusion coefficients. This has been shown to be the case in more general reversible growth models [29] and growth with mobile islands [20,30], where the scaling exponents explicitly depend on the details of the model.

We define the mean island size $\bar{s} = M_2/M_1$, where the k^{th} moment of the distribution is defined as $M_k = \sum_{s \geq 1} s^k n_s$. If the scaling of the island size distribution holds, we expect that $n_s = \theta \bar{s}^{-2} f(s/\bar{s})$, where $\bar{s} \sim \theta^\beta$, θ is the surface coverage, and $f(x)$ is a scaling function independent of coverage. In our previous work [5] we found that the scaling function is always singular, i.e. $f(x) \sim 1/x$ for $x < 1$. In order to compare the scaling function with our previous results, we will use in the following the modified scaling function of the form $g(x) = x f(x)$.

5 Results

The PCM simulations were carried out using island diffusion coefficients discussed above for Cu(100) and Cu(111), and with the detachment rate characterized by the exponent $\alpha = 1/2$. We define $\kappa = F_0/D_1$ and $\mathcal{R} = D_1/\Phi$, where D_1 is the adatom diffusion coefficient. Parameters κ and R denote the importance of detachment relative to diffusion, and of diffusion relative to deposition flux, respectively. In the simulations the corresponding values were in the ranges $10^{-6} \leq \kappa \leq 10^{-1}$ and $10^5 \leq R \leq 10^9$. The simulations show that for large detachment rates, \bar{s} and N indeed follow a power-law type of behavior, but as κ decreases, β becomes coverage-dependent, and saturates only for $\kappa \rightarrow 0$ as we have previously shown [5]. Thus, only for large κ can well-defined scaling exponents be extracted and regular island growth observed, and in this regime the island size distributions are of scaling form.

The measured values of the dynamic growth exponent β at different temperatures and large κ both for Cu(100) and Cu(111) are shown in Table 1. The exponent β seems to be temperature dependent for Cu(100) but not for Cu(111).

For Cu(100) this can be explained by examining the corresponding curves for the diffusion coefficients in Fig. 1. For small sizes (which is the case for large κ) the average slope of the diffusion coefficient curves depends strongly on temperature. If one fits a power law into the initial part of the data (for $s \leq 20$), the effective exponents are $\mu_{\text{eff}} \approx 5.4, 3.6,$ and 2.8 at $T = 300, 500,$ and 700 K, respectively. For the power-law type aggregation kernels we found [5] that the dynamic exponent behaves as $\beta = 1/(\alpha + \mu)$, when $K(i, j) \propto i^{-\mu} + j^{-\mu}$. Using the effective exponents above this prediction gives $\beta \approx 0.17, 0.24,$ and 0.30 , showing a similar trend as the measured values. If the measured values are used, somewhat smaller μ_{eff} are obtained than from the fits to the diffusion coefficient data. If the fitting is done only through maxima of the diffusion coefficient curves, a better agreement is obtained. It is also interesting to note that \bar{s} does not depend on \mathcal{R} in this regime, but only on κ . This suggests that it could be possible to tune the regime for the effective diffusion exponent on Cu(100) by changing κ . However, this effect is probably too small to be seen, since e.g. on Cu(100) at $T = 300$ K we get $\bar{s} \approx 12$ atoms for $\kappa = 10^{-3}$, and $\bar{s} \approx 7$ atoms for $\kappa = 10^{-2}$, while the differences in β between these two cases are within the errors. For Cu(111) there is no clear power-law for small sizes where the simulation data for diffusion coefficients exist. Instead, small island sizes seem to be rather mobile relative to adatoms in all temperatures.

We expect to observe scaling of island size distributions on the basis of the fact that well-defined scaling exponents exist for large detachment rates. In Fig. 3 we show scaled island size distributions for large values of detachment rates using the diffusion coefficients for Cu(100) and Cu(111) shown in Figs. 1 and 2, and setting $\alpha = 1/2$, $\mathcal{R} = 10^6$, and $\kappa = 10^{-2}$. On Cu(100) the data for different temperatures collapse to a single curve, and for $x < 1$ the scaled

T (K)	300	500	700
Cu(100)	0.25	0.34	0.43
Cu(111)	0.25	0.22	0.29*

Table 1

Dynamic scaling exponents β as defined in the text at different temperatures obtained from the PCM simulations, using the diffusion coefficients for Cu(100) and Cu(111) in Figs. 1 and 2. The asterisk for Cu(111) at $T = 700$ K indicates that the exponent is not yet constant in time. The errors in other cases are about ± 0.05 .

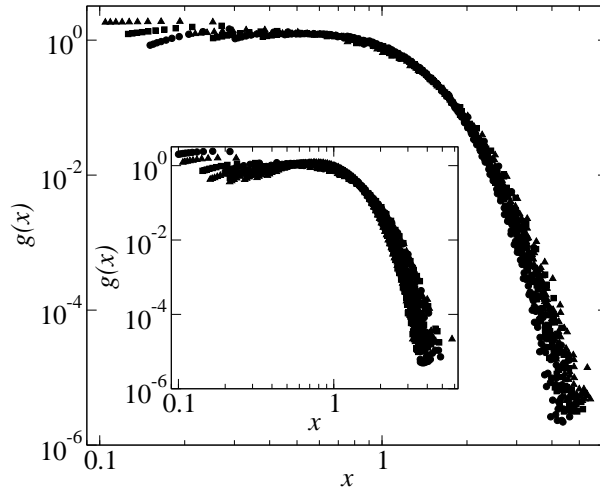


Fig. 3. The scaled island size distributions on Cu(100). The different symbols correspond to $T = 300$ K (circles), $T = 500$ K (squares), and $T = 700$ K (triangles) with $\mathcal{R} = 10^6$, $\kappa = 10^{-2}$, and $\theta \leq 0.25$ ML. The inset shows the distributions on Cu(111) with the same parameters.

distribution is almost flat. Deviations between different temperatures occur at small sizes, which reflects the differences in the diffusion coefficients. The inset shows the scaled distribution on Cu(111). In this case scaling of the distribution is not as good, and differences at small sizes are larger than on Cu(100). This reflects the fact that on Cu(111) the diffusion coefficients for small island sizes do not follow any power-law type behavior but are almost

constant in s , thus invalidating the scaling behavior as in a more simplified model for $(\mu, \alpha) = (0, 1/2)$ [6]. It is, however, expected that deviations could be seen in the large size tail of the distribution. Since the diffusion coefficients decrease several orders in magnitude, e.g. from single atoms to islands of size 10, all aggregation events leading to large sizes are basically between a small island and a large one.

6 Discussion and Conclusions

To summarize, we have studied a rate equation model with aggregation and enhanced adatom detachment corresponding to hyperthermal deposition conditions using realistic size and temperature dependent diffusion coefficients for Cu(100) and Cu(111). We have shown that qualitatively the generic features of growth, e.g. the form of the scaling function of the size distribution, are not influenced by diffusion, but quantitative predictions depend on the microscopic parameters. For example, the mean island size follows a power-law form in all cases with the exponent dependent on temperature and surface geometry. Scaling of the size distribution and the mean island size can be observed, however, only for large values of adatom detachment rates. These findings suggest that differences between various surface geometries can be observed only in the dynamic quantities such as the scaling exponent of the mean island size, but not e.g. in the scaled island size distribution which is time-independent. These predictions can be easily tested with HTD on Cu surfaces.

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